

# TK12E80W

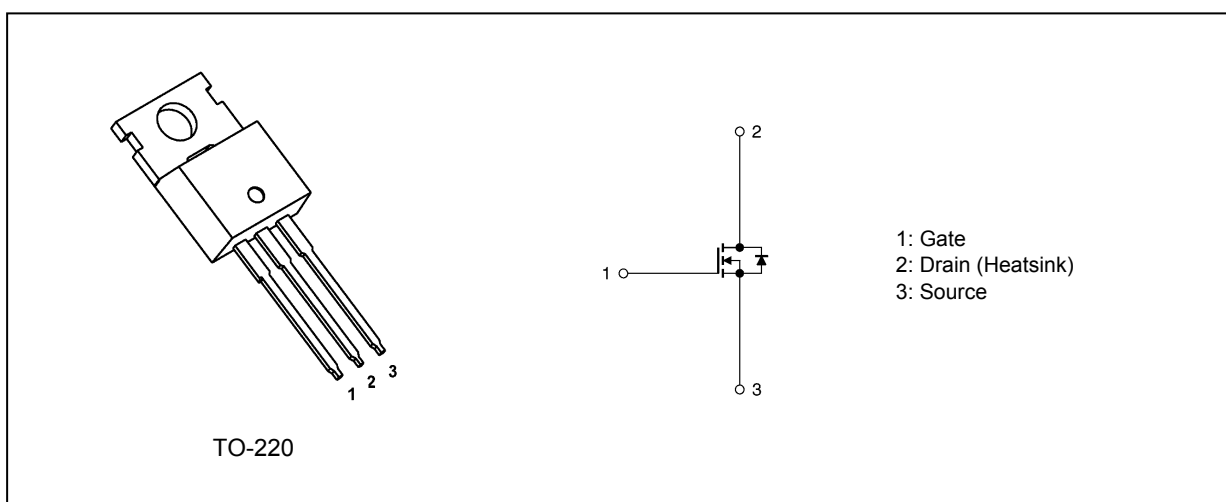
## 1. Applications

- Switching Voltage Regulators

## 2. Features

- (1) Low drain-source on-resistance:  $R_{DS(ON)} = 0.38 \Omega$  (typ.)  
by using Super Junction Structure : DTMOS
- (2) Easy to control Gate switching
- (3) Enhancement mode:  $V_{th} = 3.0$  to  $4.0$  V ( $V_{DS} = 10$  V,  $I_D = 0.57$  mA)

## 3. Packaging and Internal Circuit



## 4. Absolute Maximum Ratings (Note) ( $T_a = 25 \text{ }^\circ\text{C}$ unless otherwise specified)

| Characteristics                | Symbol                             | Rating     | Unit             |
|--------------------------------|------------------------------------|------------|------------------|
| Drain-source voltage           | $V_{DSS}$                          | 800        | V                |
| Gate-source voltage            | $V_{GSS}$                          | $\pm 20$   |                  |
| Drain current (DC)             | $I_D$ (Note 1)                     | 11.5       | A                |
| Drain current (pulsed)         | $I_{DP}$ (Note 1)                  | 46         |                  |
| Power dissipation              | $P_D$ ( $T_c = 25^\circ\text{C}$ ) | 165        | W                |
| Single-pulse avalanche energy  | $E_{AS}$ (Note 2)                  | 326        | mJ               |
| Single-pulse avalanche current | $I_{AS}$                           | 2.3        | A                |
| Reverse drain current (DC)     | $I_{DR}$ (Note 1)                  | 11.5       |                  |
| Reverse drain current (pulsed) | $I_{DRP}$ (Note 1)                 | 46         |                  |
| Channel temperature            | $T_{ch}$                           | 150        | $^\circ\text{C}$ |
| Storage temperature            | $T_{stg}$                          | -55 to 150 |                  |
| Mounting torque                | TOR                                | 0.6        | N · m            |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

## 5. Thermal Characteristics

| Characteristics                       | Symbol         | Max   | Unit |
|---------------------------------------|----------------|-------|------|
| Channel-to-case thermal resistance    | $R_{th(ch-c)}$ | 0.757 | °C/W |
| Channel-to-ambient thermal resistance | $R_{th(ch-a)}$ | 83.3  |      |

Note 1: Ensure that the channel temperature does not exceed 150 °C.

Note 2:  $V_{DD} = 90\text{ V}$ ,  $T_{ch} = 25\text{ °C}$  (initial),  $L = 112\text{ mH}$ ,  $R_G = 25\text{ }\Omega$ ,  $I_{AS} = 2.3\text{ A}$

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

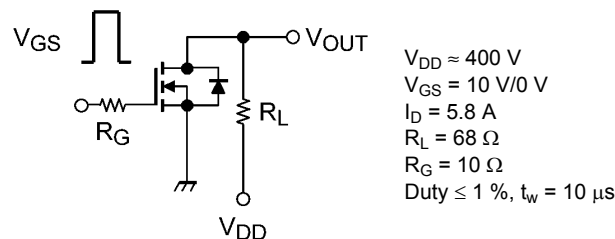
**6. Electrical Characteristics**

**6.1. Static Characteristics ( $T_a = 25\text{ }^\circ\text{C}$  unless otherwise specified)**

| Characteristics                | Symbol        | Test Condition                                  | Min | Typ. | Max     | Unit          |
|--------------------------------|---------------|---|-----|------|---------|---------------|
| Gate leakage current           | $I_{GSS}$     | $V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$ | —   | —    | $\pm 1$ | $\mu\text{A}$ |
| Drain cut-off current          | $I_{DSS}$     | $V_{DS} = 800\text{ V}, V_{GS} = 0\text{ V}$    | —   | —    | 10      |               |
| Drain-source breakdown voltage | $V_{(BR)DSS}$ | $I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$       | 800 | —    | —       | V             |
| Gate threshold voltage         | $V_{th}$      | $V_{DS} = 10\text{ V}, I_D = 0.57\text{ mA}$    | 3.0 | —    | 4.0     |               |
| Drain-source on-resistance     | $R_{DS(ON)}$  | $V_{GS} = 10\text{ V}, I_D = 5.8\text{ A}$      | —   | 0.38 | 0.45    | $\Omega$      |

**6.2. Dynamic Characteristics ( $T_a = 25\text{ }^\circ\text{C}$  unless otherwise specified)**

| Characteristics                | Symbol      | Test Condition   | Min | Typ. | Max | Unit        |
|--------------------------------|-------------|--|-----|------|-----|-------------|
| Input capacitance              | $C_{iss}$   | $V_{DS} = 300\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$ | —   | 1400 | —   | $\text{pF}$ |
| Reverse transfer capacitance   | $C_{rss}$   |  | —   | 3    | —   |             |
| Output capacitance             | $C_{oss}$   |  | —   | 29   | —   |             |
| Effective output capacitance   | $C_{o(er)}$ | $V_{DS} = 0\text{ to }640\text{ V}, V_{GS} = 0\text{ V}$       | —   | 35   | —   |             |
| Gate resistance                | $r_g$       | $V_{DS} = \text{OPEN}, f = 1\text{ MHz}$                       | —   | 30   | —   | $\Omega$    |
| Switching time (rise time)     | $t_r$       | See Figure 6.2.1   | —   | 40   | —   | ns          |
| Switching time (turn-on time)  | $t_{on}$    |  | —   | 70   | —   |             |
| Switching time (fall time)     | $t_f$       |  | —   | 11   | —   |             |
| Switching time (turn-off time) | $t_{off}$   |  | —   | 130  | —   |             |
| MOSFET dv/dt ruggedness        | dv/dt       | $V_{DS} \leq V_{(BR)DSS}, I_D \leq 11.5\text{ A}$              | 50  | —    | —   | V/ns        |



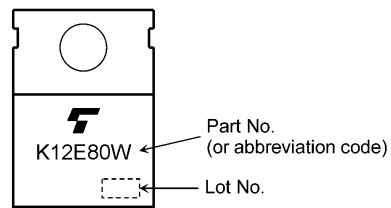
**Fig. 6.2.1 Switching Time Test Circuit**

**6.3. Gate Charge Characteristics ( $T_a = 25\text{ }^\circ\text{C}$  unless otherwise specified)**

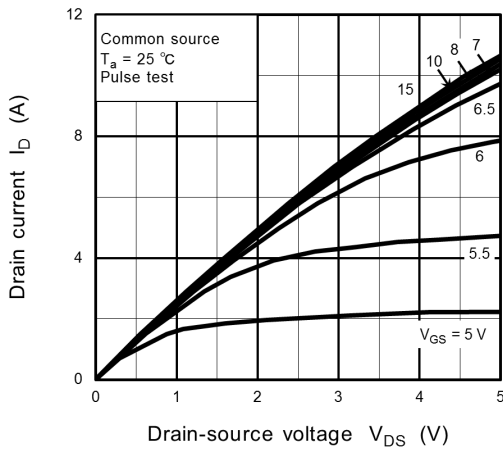
| Characteristics                                 | Symbol    | Test Condition   | Min | Typ. | Max | Unit |
|---|-----------|--|-----|------|-----|------|
| Total gate charge (gate-source plus gate-drain) | $Q_g$     | $V_{DD} \approx 640\text{ V}, V_{GS} = 10\text{ V}, I_D = 11.5\text{ A}$ | —   | 23   | —   | nC   |
| Gate-source charge 1                            | $Q_{gs1}$ |  | —   | 8    | —   |      |
| Gate-drain charge                               | $Q_{gd}$  |  | —   | 7.5  | —   |      |

**6.4. Source-Drain Characteristics ( $T_a = 25\text{ }^\circ\text{C}$  unless otherwise specified)**

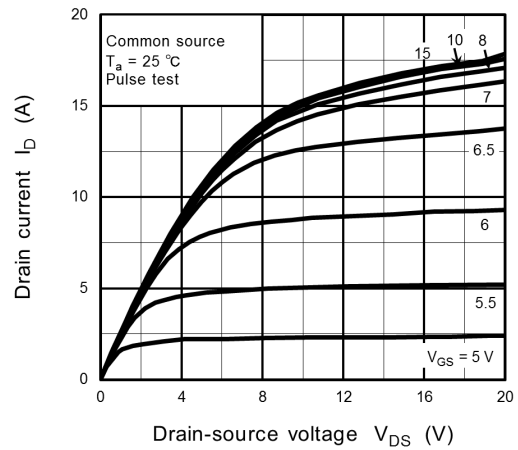
| Characteristics               | Symbol    | Test Condition  | Min | Typ. | Max  | Unit          |
|-------------------------------|-----------|---|-----|------|------|---------------|
| Diode forward voltage         | $V_{DSF}$ | $I_{DR} = 11.5\text{ A}, V_{GS} = 0\text{ V}$   | —   | —    | -1.7 | V             |
| Reverse recovery time         | $t_{rr}$  | $V_{DD} \approx 640\text{ V}$<br>$I_{DR} = 5.8\text{ A}, V_{GS} = 0\text{ V}$<br>$-di_{DR}/dt = 100\text{ A}/\mu\text{s}$ | —   | 330  | —    | ns            |
| Reverse recovery charge       | $Q_{rr}$  |   | —   | 3.6  | —    | $\mu\text{C}$ |
| Peak reverse recovery current | $I_{rr}$  |   | —   | 22   | —    | A             |
| Diode dv/dt ruggedness        | dv/dt     | $V_{DS} \leq 640\text{ V}, I_{DR} \leq 5.8\text{ A}, V_{GS} = 0\text{ V}$   | 4.5 | —    | —    | V/ns          |

**7. Marking****Fig. 7.1 Marking**

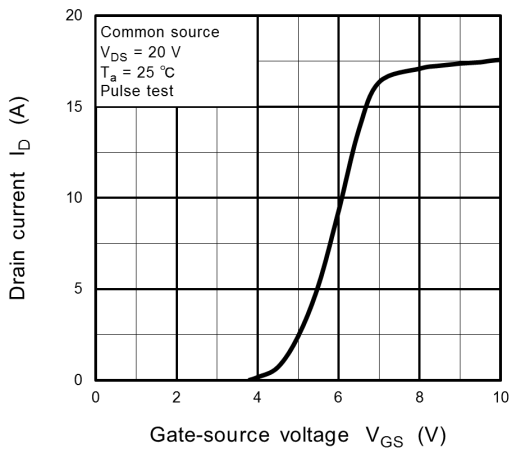
**8. Characteristics Curves (Note)**



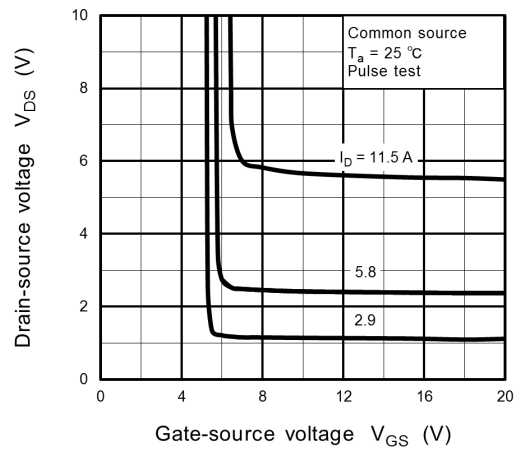
**Fig. 8.1  $I_D - V_{DS}$**



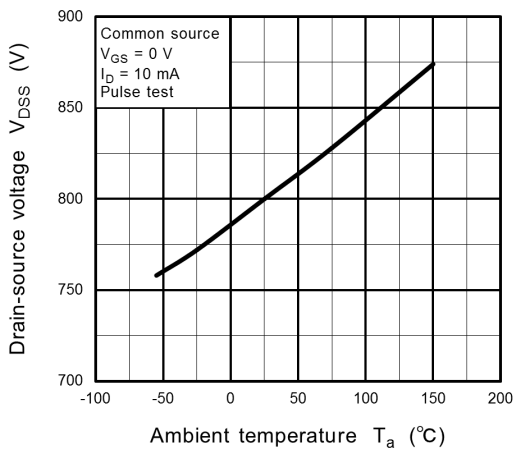
**Fig. 8.2  $I_D - V_{DS}$**



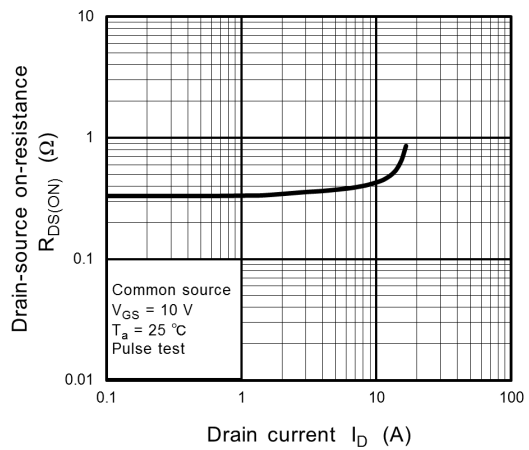
**Fig. 8.3  $I_D - V_{GS}$**



**Fig. 8.4  $V_{DS} - V_{GS}$**



**Fig. 8.5  $V_{DSS} - T_a$**



**Fig. 8.6  $R_{DS(ON)} - I_D$**

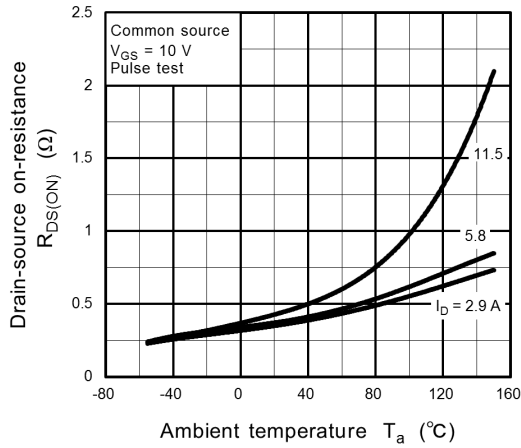


Fig. 8.7  $R_{DS(ON)} - T_a$

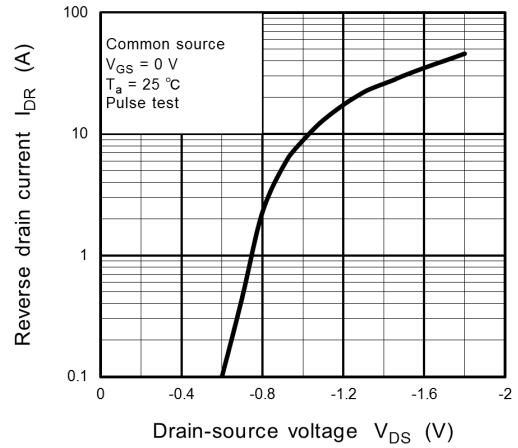


Fig. 8.8  $I_{DR} - V_{DS}$

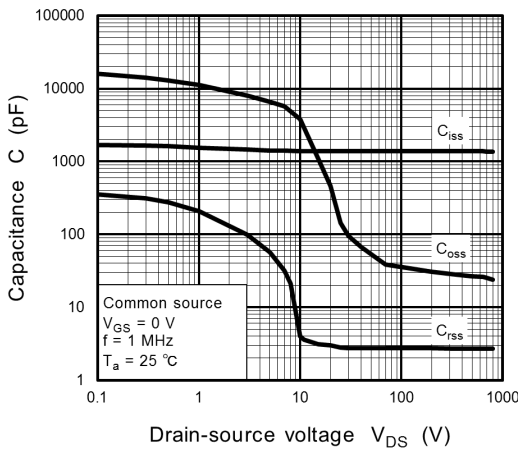


Fig. 8.9  $C - V_{DS}$

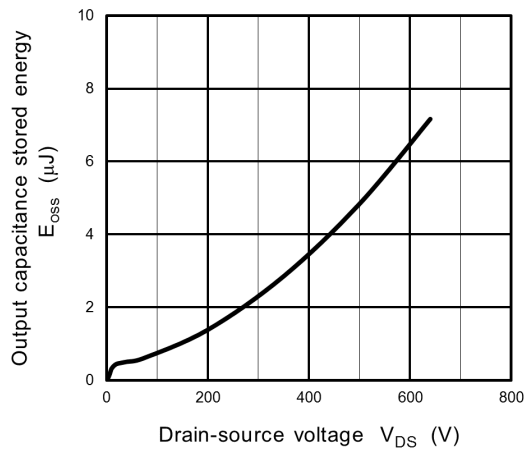


Fig. 8.10  $E_{oss} - V_{DS}$

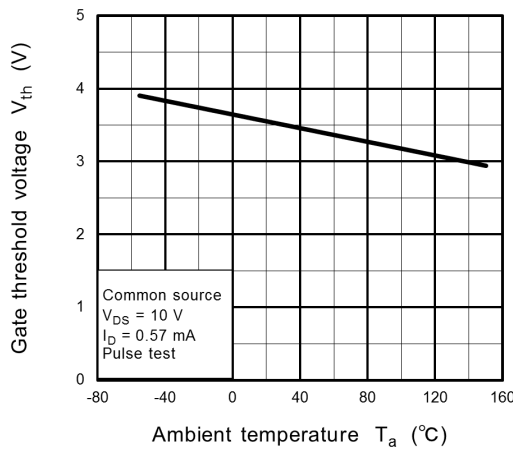


Fig. 8.11  $V_{th} - T_a$

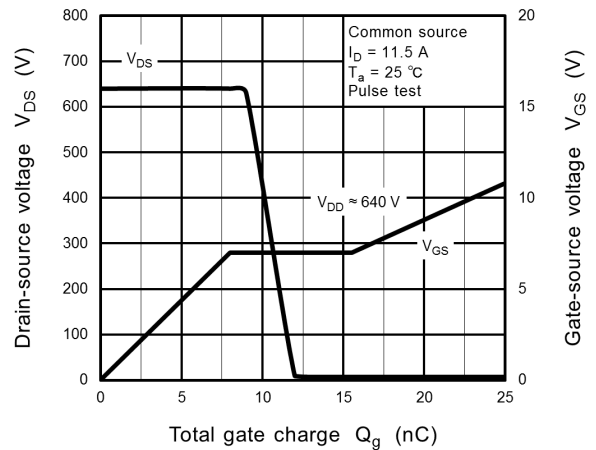
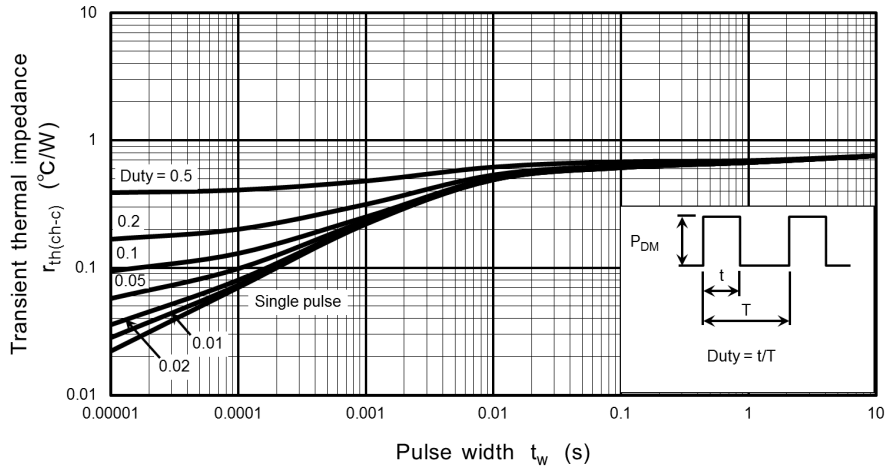
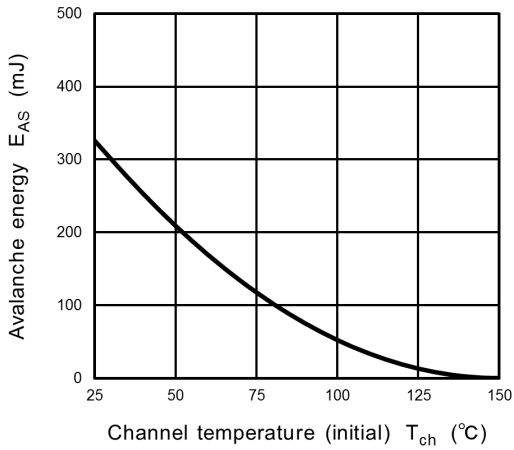


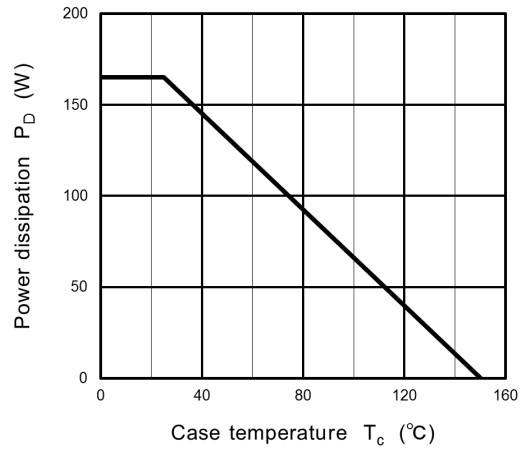
Fig. 8.12 Dynamic Input/Output Characteristics



**Fig. 8.13  $r_{th} - t_w$**   
(Guaranteed Maximum)



**Fig. 8.14  $E_{AS} - T_{ch}$**   
(Guaranteed Maximum)

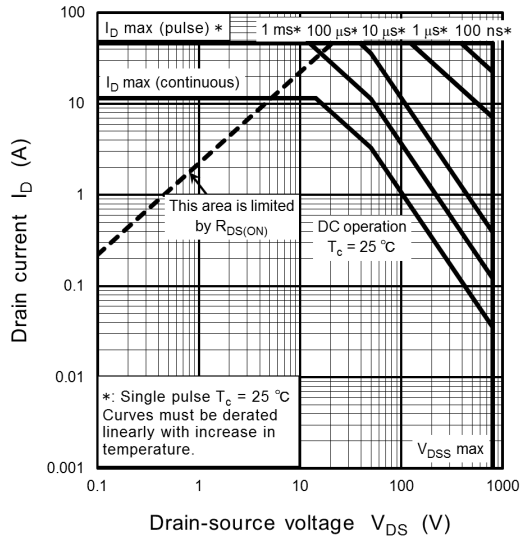


**Fig. 8.15  $P_D - T_c$**   
(Guaranteed Maximum)



$$R_G = 25 \Omega, V_{DD} = 90 \text{ V } E_{AS} = \frac{1}{2} \cdot L \cdot I_{AS}^2 \cdot \left( \frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$

**Fig. 8.16 Test Circuit/Waveform**



**Fig. 8.17 Safe Operating Area (Guaranteed Maximum)**

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



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